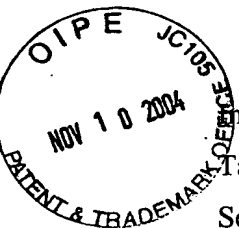


LFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re patent application of

Tae-Hee CHOE, et al.

Serial No. 10/713,216

Filed: November 17, 2003

For: SOI SUBSTRATE HAVING AN ETCH
STOP LAYER, AND FABRICATION
METHOD THEREOF, SOI INTEGRATED
CIRCUIT FABRICATED THEREON, AND
METHOD OF FABRICATING SOI
INTEGRATED CIRCUIT USING THE SAME

Art Unit: 2815

Examiner: E.J. Wojchiechowicz

Confirmation No.: 2454

Atty. Docket No. 239/156 DIV

AMENDMENT UNDER 37 C.F.R. § 1.111

Mail Stop Amendment
Commissioner for Patents
Alexandria, VA 22313-1450

Sir:

INTRODUCTORY COMMENTS

In response to the Office action mailed August 11, 2004, the following amendments and remarks are respectfully submitted in connection with the above-identified application:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in a listing of claims, which begins on page 3 of this paper.

Remarks begin on page 11 of this paper.

A replacement Abstract of the Disclosure is attached at page 15.